

MOSFETs Silicon P-Channel MOS

# SSM6J512NU

#### 1. Applications

· Power Management Switches

#### 2. Features

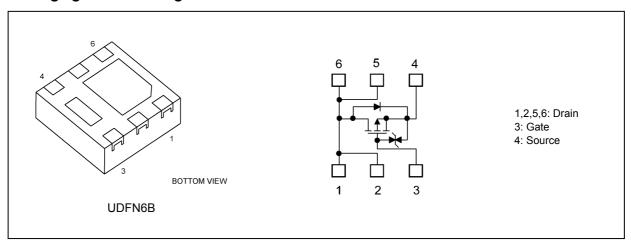
- (1) 1.8 V gate drive voltage.
- (2) Low drain-source on-resistance

 $R_{DS(ON)} = 24.0 \text{ m}\Omega \text{ (typ.) } (@V_{GS} = -1.8 \text{ V})$ 

 $R_{\rm DS(ON)} = 18.3 \ {\rm m}\Omega \ ({\rm typ.}) \ (@V_{\rm GS} = -2.5 \ {\rm V})$ 

 $R_{\rm DS(ON)} = 14.3 \ {\rm m}\Omega \ ({\rm typ.}) \ (@V_{\rm GS} = -4.5 \ {\rm V})$ 

#### 3. Packaging and Pin Assignment



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	-12	V
Gate-source voltage				$V_{GSS}$	±10	V
Drain current			(Note 1)	$I_D$	-10	Α
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	-30	Α
Power dissipation			(Note 3)	$P_{D}$	1.25	W
Power dissipation		$t \le 10 \text{ s}$	(Note 3)	$P_D$	2.5	W
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: Pulse width (PW)  $\leq$ 10 ms, duty  $\leq$  1 %

Note 3: Device mounted on a FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ mm}, \text{Cu Pad} : 645 \text{ mm}^2)$ 

Start of commercial production

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -12 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-12	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 5 V	-7	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$	-0.3	_	-1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D = -4 A$ , $V_{GS} = -8.0 V$	_	12.4	16.2	mΩ
			I <sub>D</sub> = -4 A, V <sub>GS</sub> = -4.5 V	_	14.3	18.7	
			I <sub>D</sub> = -4 A, V <sub>GS</sub> = -3.6 V	_	15.4	20.5	
			I <sub>D</sub> = -4 A, V <sub>GS</sub> = -2.5 V	_	18.3	25.7	
			I <sub>D</sub> = -4 A, V <sub>GS</sub> = -1.8 V	_	24.0	40.1	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -2 \text{ A}$	_	17		S

- Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

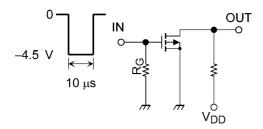
  Take this into consideration when using the device.

Note 3: Pulse measurement.

# 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V},$	_	1400		pF
Reverse transfer capacitance		f = 1 MHz	_	225		
Output capacitance	C <sub>oss</sub>		_	250	_	
Switching time (turn-on time)		$V_{DD} = -6 \text{ V}, I_{D} = -10 \text{ A}$	_	77	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to -4.5 V, $R_{G}$ = 10 $\Omega$	_	350	_	

### 5.3. Switching Time Test Circuit



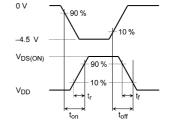


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = -6 \text{ V}, V_{GS} = -4.5 \text{ V},$	_	19.5	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$I_D = -6 A$	_	1.4	_	
Gate-drain charge	$Q_{gd}$		_	9.0		

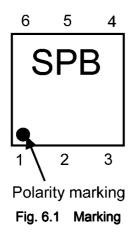


# 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (I	Note 1)	V <sub>DSF</sub>	I <sub>D</sub> = 4 A, V <sub>GS</sub> = 0 V	_	0.75	1.1	V

Note 1: Pulse measurement.

## 6. Marking



Drain

Source

1 2 3

Polarity marking (on the top)
\*Electrodes: on the bottom

Fig. 6.2 Pin Conditioon (Top View)

#### 7. Characteristics Curves (Note)

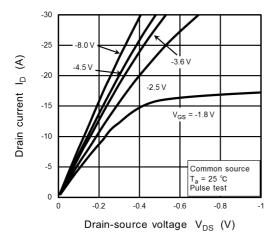
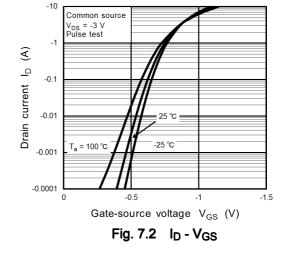


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>



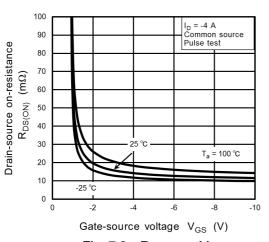


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

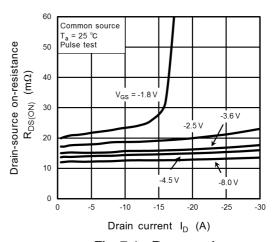


Fig. 7.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

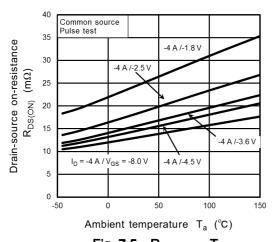


Fig. 7.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

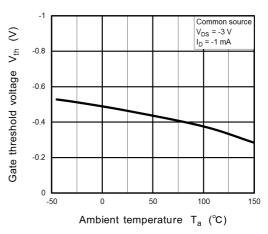


Fig. 7.6 V<sub>th</sub> - T<sub>a</sub>

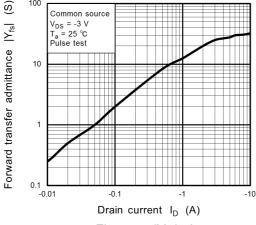


Fig. 7.7  $|Y_{fs}|$  -  $I_D$ 

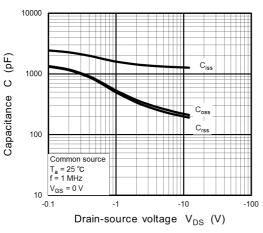


Fig. 7.9 C - V<sub>DS</sub>

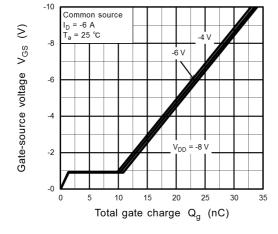


Fig. 7.11 Dynamic Input Characteristics

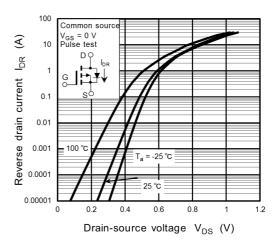


Fig. 7.8 I<sub>DR</sub> - V<sub>DS</sub>

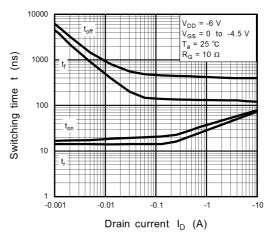


Fig. 7.10 t-I<sub>D</sub>

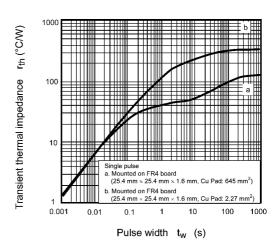


Fig. 7.12 rth - tw

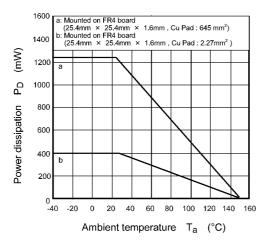


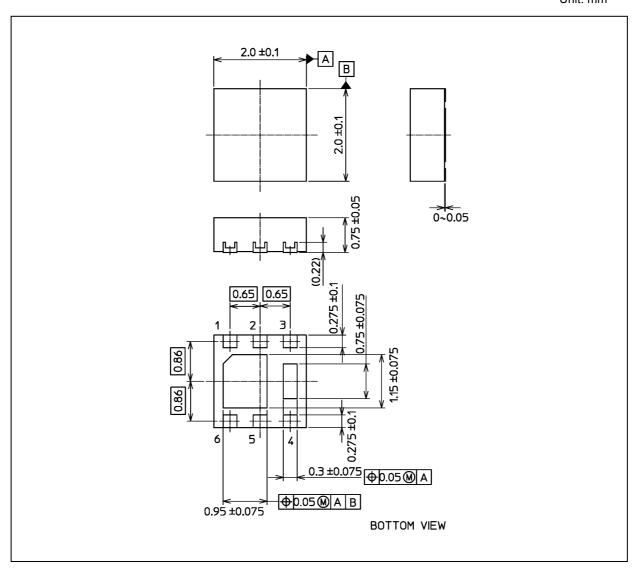
Fig. 7.13 PD - Ta

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
Nickname: UDFN6B	



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